

IN THE SPECIFICATION:

Please replace paragraph number [0015] with the following rewritten paragraph:

[0015] The present invention comprises a semiconductor device package including an interposer and a plurality of semiconductor devices in a vertical or stacked arrangement. The invention includes various embodiments of the device package and methods for assembling and packaging two or more semiconductor devices with an interposer. The semiconductor device package may comprise a chip scale multichip package (CSMCP) which is configurable in various ways for use in a variety of applications, including as a memory package. The package may be formed with a thickness not much greater than the cumulative thicknesses of the devices and, also, may have a relatively small “footprint”. “footprint.”

Please replace paragraph number [0100] with the following rewritten paragraph:

[0100] As shown in FIG. 14D, a first-level semiconductor device 20 is flip-chip bonded, by discrete conductive elements 36 (not shown), to the active surface 42 of each second-level semiconductor device 40 on wafer 46. Metallization (not visible) on the active surface 42 of wafer 46 connects the circuits (not visible) of both semiconductor devices 20, 40 of each two-die unit 94 (FIG. 14E) to peripheral discrete conductive elements 56, e.g., solder balls on each second-level semiconductor device 40. Wafer 46 may be cut along saw lines 48 to singulate the two-die units 94, each of which comprises a first-level semiconductor device 20 flip-chip bonded to a second-level semiconductor device 40, as shown in FIG. 14E. Alternatively, wafer 46 may be severed prior to securing or electrically connecting first-level semiconductor devices 20 to second-level semiconductor devices 40.